

Octal D-Type Latch with 3-State Output

MC74VHC573, MC74VHCT573A

The MC74VHC573/MC74VHCT573A is an advanced high speed CMOS octal latch with 3-state output fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The 8-bit D-type latch is controlled by a latch enable input and an output enable input. When the output enable input is high, the eight outputs are in a high impedance state.

The MC74VHC573 inputs are compatible with standard CMOS levels while the MC74VHCT573A inputs are compatible with TTL levels. The MC74VHCT573A device can be used as a level converter for interfacing 3.3 V to 5.0 V, because it has full 5.0 V CMOS level output swings.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The MC74VHC573 and MC74VHCT573A inputs tolerate voltages up to 5.5 V, allowing the interface of 5 V systems to 3 V systems.

The MC74VHCT573A output structures provide protection when VCC = 0 V. These output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

Features

- High Speed: $t_{PD} = 4.5 \text{ ns (Typ)}$ at $V_{CC} = 5.0 \text{ V (VHC)}$ $t_{PD} = 7.7 \text{ ns (Typ)}$ at $V_{CC} = 5.0 \text{ V (VHCT)}$
- Low Power Dissipation: $I_{CC} = 4.0 \,\mu\text{A}$ (Max) at $T_A = 25^{\circ}\text{C}$
- High Noise Immunity: V_{NIH} = V_{NII} = 28%
- Power Down Protection Provided
- Balanced Propagation Delays
- Designed for: 2.0 V to 5.5 V (VHC)

4.5 V to 5.5 V (VHCT)

• Low Noise: $V_{OLP} = 1.2 \text{ V (Max) (VHC)}$

 $V_{OLP} = 1.6 \text{ V (Max) (VHCT)}$

- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 100 mA
- ESD Performance: Human Body Model > 2000 V;
- Chip Complexity: 234 FETs or 58.5 Equivalent Gates
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

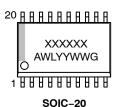


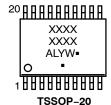
SOIC-20 DW SUFFIX CASE 751D



TSSOP-20 DT SUFFIX CASE 948E

MARKING DIAGRAMS





A = Assembly Location

WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week
G or • = Pb-Free Package

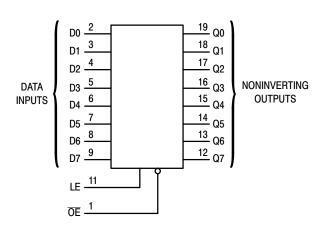
(Note: Microdot may be in either location)

PIN ASSIGNMENT

OE	00
Dada to be	
D1 [] 3 18 [] G	≀1
D2 [4 17] G)2
D3 [5 16] C)3
D4 [6 15] G)4
D5 [7 14] G)5
D6 [8 13] G)6
D7 [9 12] G)7
GND [10 11] L	Ε

ORDERING INFORMATION

See detailed ordering and shipping information on page 9 of this data sheet.



FUNCTION TABLE

	INPUTS	OUTPUT	
OE	LE	D	q
L L H	HHLX	HLXX	H L No Change Z

Figure 1. Logic Diagram

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +6.5	V
V _{IN}	DC Input Voltage		-0.5 to +6.5	V
V _{OUT}	DC Output Voltage (MC74VHC)		-0.5 to V _{CC} +0.5	V
	DC Output Voltage (MC74VHCT) Active Mode (High or Tristate Mo	de (Note 1)	-0.5 to V _{CC} +0.5 -0.5 to +6.5 -0.5 to +6.5	
I _{IN}	DC Input Current, per Pin		±20	mA
I _{OUT}	DC Output Current, Per Pin		±25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins		±75	mA
I _{IK}	Input Clamp Current		-20	mA
Іок	Output Clamp Current	MC74VHC MC74VHCT	±20 -20	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 secs		260	°C
TJ	Junction Temperature Under Bias		+150	°C
$\theta_{\sf JA}$,	SOIC-20W TSSOP-20	96 150	°C/W
P _D		SOIC-20W TSSOP-20	1302 833	mW
MSL	Moisture Sensitivity		Level 1	-
F _R	Flammability Rating Oxygen Inde	ex: 28 to 34	UL 94 V-0 @ 0.573 in	-
V _{ESD}	3 ()	Body Model evice Model	2000 N/A	V
I _{LATCHUP}	Latchup Performance (Note 4)		±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Applicable to devices with outputs that may be tri–stated.

- Applicable to devices with outputs that may be the stated.
 Measured with minimum pad spacing on an FR4 board, using 76 mm-by-114 mm, 2-ounce copper trace no air flow per JESD51-7.
 HBM tested to EIA / JESD22-A114-A. CDM tested to JESD22-C101-A. JEDEC recommends that ESD qualification to EIA/JESD22-A115A (Machine Model) be discontinued.
- Tested to EIA/JESD78 Class II.

RECOMMENDED OPERATING CONDITIONS

Symbol	P	Min	Max	Unit	
MC74VHC				•	•
V _{CC}	DC Supply Voltage		2.0	5.5	V
V _{IN}	DC Input Voltage (Note 5)		0	5.5	V
V _{OUT}	DC Output Voltage (Note 5)		0	V _{CC}	V
T _A	Operating Temperature		-55	+85	°C
t _r , t _f	Input Rise or Fall Rate	V _{CC} = 3.0 V to 3.6 V V _{CC} = 4.5 V to 5.5 V	0 0	100 20	ns/V
MC74VHC	Т			•	•
V _{CC}	DC Supply Voltage		4.5	5.5	V
V _{IN}	DC Input Voltage (Note 5)		0	5.5	V
V _{OUT}	DC Output Voltage (Note 5)	Active Mode (High or Low State) Tristate Mode Power-Off Mode (V_{CC} = 0 V)	0 0 0	V _{CC} 5.5 5.5	V
T _A	Operating Temperature		-55	+85	°C
t _r , t _f	Input Rise or Fall Rate	V _{CC} = 4.5 V to 5.5 V	0	20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

5. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

DC ELECTRICAL CHARACTERISTICS (MC74VHC573)

			V _{CC}	,	T _A = 25°C	;	T _A = - 40	0 to 85°C	
Symbol	Parameter	Test Conditions	v	Min	Тур	Max	Min	Max	Unit
V _{IH}	Minimum High-Level Input Voltage		2.0 3.0 to 5.5	1.50 V _{CC} x 0.7			1.50 V _{CC} x 0.7		V
V _{IL}	Maximum Low-Level Input Voltage		2.0 3.0 to 5.5			0.50 V _{CC} x 0.3		0.50 V _{CC} x 0.3	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu\text{A}$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		V
		$\begin{aligned} V_{in} &= V_{IH} \text{ or } V_{IL} \\ I_{OH} &= -4 \text{ mA} \\ I_{OH} &= -8 \text{ mA} \end{aligned}$	3.0 4.5	2.58 3.94			2.48 3.80		
V _{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu\text{A}$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1	٧
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 4m \text{ A}$ $I_{OL} = 8 \text{ mA}$	3.0 4.5			0.36 0.36		0.44 0.44	
I _{in}	Maximum Input Leakage Current	V _{in} = 5.5 V or GND	0 to 5.5			±0.1		±1.0	μΑ
l _{OZ}	Maximum Three-State Leakage Current	$V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or GND}$	5.5			±0.25		±2.5	μΑ
I _{CC}	Maximum Quiescent Supply Current	V _{in} = V _{CC} or GND	5.5			4.0		40.0	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS (MC74VHC573)

				T _A = 25°C	;	T _A = - 40	0 to 85°C	
Symbol	Parameter	Test Conditions	Min	Тур	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, LE to Q	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		7.6 10.1	11.9 15.4	1.0 1.0	14.0 17.5	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		5.0 6.5	7.7 9.7	1.0 1.0	9.0 11.0	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, D to Q	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		7.0 9.5	11.0 14.5	1.0 1.0	13.0 16.5	ns
		V_{CC} = 5.0 ± 0.5 V C_L = 15 pF C_L = 50 pF		4.5 6.0	6.8 8.8	1.0 1.0	8.0 10.0	
t _{PZL} , t _{PZH}	Output Enable Time, OE to Q	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		7.3 9.8	11.5 15.0	1.0 1.0	13.5 17.0	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		5.2 6.7	7.7 9.7	1.0 1.0	9.0 11.0	
t _{PLZ} ,	Output Disable Time, OE to Q	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $C_L = 50 \text{ pF}$		10.7	14.5	1.0	16.5	ns
t _{PHZ}	OE to Q	$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $C_L = 50 \text{ pF}$		6.7	9.7	1.0	11.0	
t _{OSLH} , t _{OSHL}	Output to Output Skew	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $C_L = 50 \text{ pF}$ (Note 6)			1.5		1.5	ns
		$V_{CC} = 5.5 \pm 0.5 \text{ V}$ $C_L = 50 \text{ pF}$ (Note 6)			1.0		1.0	ns
C _{in}	Maximum Input Capacitance			4	10		10	pF
C _{out}	Maximum Three-State Output Capacitance (Output in High-Im- pedance State)			6				pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Note 7)	29	pF

NOISE CHARACTERISTICS (MC74VHC573) ($C_L = 50 \text{ pF}, V_{CC} = 5.0 \text{ V}$)

		T _A = 25°C		
Symbol	Parameter	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.9	1.2	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.9	-1.2	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		3.5	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		1.5	V

TIMING REQUIREMENTS (MC74VHC573)

			T _A = 25°C		T _A = - 40 to 85°C	
Symbol	Parameter	Test Conditions	Тур	Limit	Limit	Unit
t _{w(h)}	Minimum Pulse Width, LE	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \pm 0.5 \text{ V}$		5.0 5.0	5.0 5.0	ns
t _{su}	Minimum Setup Time, D to LE	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \pm 0.5 \text{ V}$		3.5 3.5	3.5 3.5	ns
t _h	Minimum Hold Time, D to LE	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \pm 0.5 \text{ V}$		1.5 1.5	1.5 1.5	ns

Parameter guaranteed by design. t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|.
 C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/8 (per latch). C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

DC ELECTRICAL CHARACTERISTICS (MC74VHCT573A)

			V _{CC}	-	T _A = 25	°C	$T_A = -40$) to 85°C	
Symbol	Parameter	Test Conditions	v	Min	Тур	Max	Min	Max	Unit
V _{IH}	Minimum High-Level Input Voltage		4.5 to 5.5	2.0			2.0		V
V _{IL}	Maximum Low-Level Input Voltage		4.5 to 5.5			0.8		0.8	V
V _{OH}	Minimum High-Level Output	I _{OH} = - 50 μA	4.5	4.4	4.5		4.4		V
	Voltage $V_{in} = V_{IH}$ or V_{IL}	I _{OH} = – 8 mA	4.5	3.94			3.80		
V _{OL}	Maximum Low-Level Output	I _{OL} = 50 μA	4.5		0.0	0.1		0.1	V
	Voltage $V_{in} = V_{IH}$ or V_{IL}	I _{OL} = 8 mA	4.5			0.36		0.44	
I _{in}	Maximum Input Leakage Current	V _{in} = 5.5 V or GND	0 to 5.5			±[0.1		±1.0	μΑ
l _{OZ}	Maximum 3-State Leakage Current	$V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or GND}$	5.5			± 0.25		±2.5	μΑ
I _{CC}	Maximum Quiescent Supply Current	V _{in} = V _{CC} or GND	5.5			4.0		40.0	μΑ
I _{CCT}	Quiescent Supply Current	Per Input: V _{IN} = 3.4 V Other Input: V _{CC} or GND	5.5			1.35		1.50	mA
I _{OPD}	Output Leakage Current	V _{OUT} = 5.5 V	0			0.5		5.0	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS (MC74VHCT573A)

				T _A = 25°C		$T_A = -40$) to 85°C		
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, LE to Q	$V_{CC} = 5.0 \pm 0.5 \text{ V}$	C _L = 15 pF C _L = 50 pF		7.7 8.5	12.3 13.3	1.0 1.0	13.5 14.5	ns
t _{PLH} , t _{PHL}	Maximum Propagation Delay, D to Q	$V_{CC} = 5.0 \pm 0.5 \text{ V}$	C _L = 15 pF C _L = 50 pF		5.1 5.9	8.5 9.5	1.0 1.0	9.5 10.5	ns
t _{PZL} , t _{PZH}	Output Enable Time, OE to Q	$V_{CC} = 5.0 \pm 0.5 \text{ V}$	C _L = 15 pF C _L = 50 pF		6.3 7.1	10.9 11.9	1.0 1.0	12.5 13.5	ns
t _{PLZ} , t _{PHZ}	Output Disable Time, OE to Q	$V_{CC} = 5.0 \pm 0.5 \text{ V}$	C _L = 50 pF		8.8	11.2	1.0	12.0	ns
t _{OSLH} , t _{OSHL}	Output to Output Skew	V _{CC} = 5.5 ± 0.5 V (Note 8)	C _L = 50 pF			1.0		1.0	ns
C _{in}	Maximum Input Capacitance				4	10		10	pF
C _{out}	Maximum 3–State Output Capacitance (Output in High-Impedance State)				6				pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Note 9)	25	pF

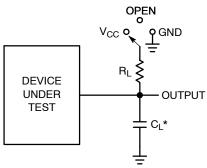
Parameter guaranteed by design. t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|.
 C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/8 (per latch). C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

NOISE CHARACTERISTICS (MC74VHCT573A) ($C_L = 50 \text{ pF}, V_{CC} = 5.0 \text{ V}$)

		T _A = 25°C		
Symbol	Parameter	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	1.2	1.6	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-1.2	-1.6	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V

TIMING REQUIREMENTS (MC74VHCT573A)

			T _A = 25°C		T _A = - 40 to 85°C	
Symbol	Parameter	Test Conditions	Тур	Limit	Limit	Unit
t _{w(h)}	Minimum Pulse Width, LE	$V_{CC} = 5.0 \pm 0.5 V$		6.5	8.5	ns
t _{su}	Minimum Setup Time, D to LE	$V_{CC} = 5.0 \pm 0.5 V$		1.5	1.5	ns
t _h	Minimum Hold Time, D to LE	$V_{CC} = 5.0 \pm 0.5 V$		3.5	3.5	ns



 $^{^{\}star}C_{L}$ Includes probe and jig capacitance Input signal t_{R} = t_{F} = 3 ns

Test	Switch Position	C _L	R _L
t _{PLH} / t _{PHL}	Open	See AC Characteristics	1 kΩ
t _{PLZ} / t _{PZL}	V _{CC}	Table	
t _{PHZ} / t _{PZH}	GND		

Figure 2. Test Circuits

SWITCHING WAVEFORMS

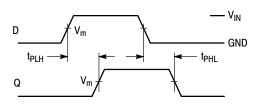


Figure 1.

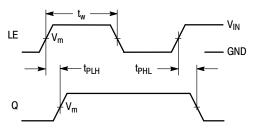
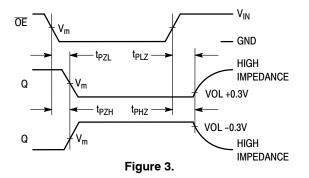


Figure 2.



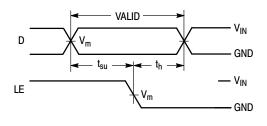


Figure 4.

Device	V _{IN} , V	V _m , V
MC74VHC573	V _{CC}	50% x V _{CC}
MC74VHCT573A	3 V	1.5 V

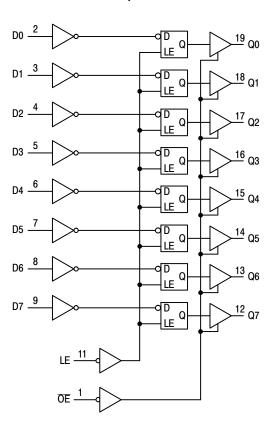


Figure 5. Expanded Logic Diagram

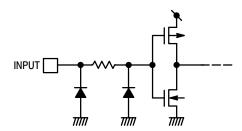


Figure 6. Input Equivalent Circuit

ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
MC74VHC573DWR2G	VHC573G	SOIC-20 WB	1000 Units / Tape & Reel
MC74VHC573DTR2G	VHC 573	TSSOP-20	2500 Units / Tape & Reel
MC74VHCT573ADWR2G	VHCT573AG	SOIC-20 WB	1000 Units / Tape & Reel
MC74VHCT573ADTG	VHCT 573A	TSSOP-20	75 Units / Rail
MC74VHCT573ADTR2G	VHCT 573A	TSSOP-20	2500 Units / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*-}Q Suffix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable

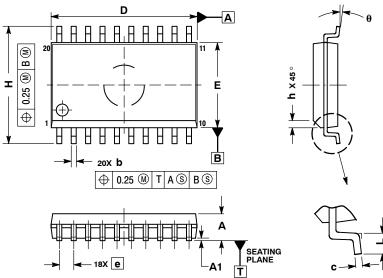




SOIC-20 WB CASE 751D-05 **ISSUE H**

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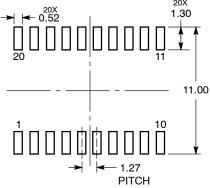




- DIMENSIONS ARE IN MILLIMETERS.
 INTERPRET DIMENSIONS AND TOLERANCES.
- PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD
- PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL

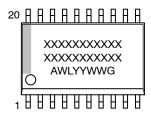
	MILLIMETERS			
DIM	MIN	MAX		
Α	2.35	2.65		
A1	0.10	0.25		
b	0.35	0.49		
С	0.23	0.32		
D	12.65	12.95		
E	7.40	7.60		
е	1.27	BSC		
Н	10.05	10.55		
h	0.25	0.75		
L	0.50	0.90		
A	0 °	7 °		

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location

WL = Wafer Lot ΥY = Year WW = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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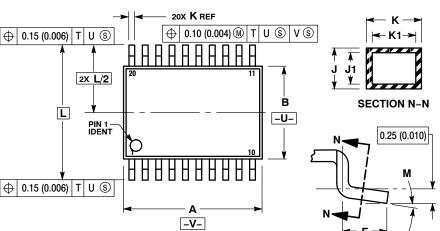
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^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

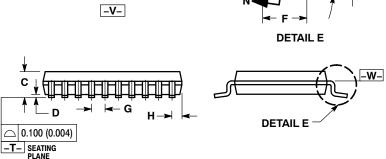


TSSOP-20 WB CASE 948E ISSUE D

DATE 17 FEB 2016



- 7.06



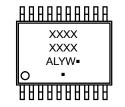
NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
- 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K
- (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 7. DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-

	MILLIN	IETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026 BSC	
Н	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
М	٥°	gο	٥°	g٥

GENERIC SOLDERING FOOTPRINT MARKING DIAGRAM*



= Assembly Location

= Wafer Lot

= Year

= Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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DIMENSIONS: MILLIMETERS

0.65

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0.36

16X

1.26

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